

GHXS400A120S7D5

VDC	1200 V
I _F	400 A
T _j ,max	150 °C

1200V SiC Power Module Half Bridge

Features

- · SiC Schottky Diode
- Zero reverse recovery
- Zero forward recovery
- Temperature independent switching behavior
- Positive Temperature coefficient on V_F
- · Low stray inductance
- · High junction temperature operation
- · All parts tested to greater than 1,400V

Semio GHXS400A120S7DS POR SEE OF SEE

Package

Half Bridge

Benefits

- Outstanding performance at high frequency operation
- · Low loss and low EMI noise
- Very rugged and easy mounting
- Direct mounting to heatsink (isolated package)
- · Low junction to case thermal resistance
- · RoHS compliant

Part #	Package	Marking
GHXS400A120S7D5	S 7	GHXS400A120S7D5

Applications

- · Switched-mode power supplies
- Induction heater
- Welding equipment
- · Charging station



Maximum Ratings, at T_i=25 °C, unless otherwise specified (per leg)

Characteristics	Symbol	Conditions	Values	Unit
		T _C =25 °C, T _j =150 °C	623	
Continuous forward current	I _{F*}	T _C =93 °C, T _j =150 °C	400	Α
		T _C =125 °C, T _j =150 °C	224	
Repetitive peak reverse voltage	V_{RRM}	T _j =25 °C	1200	V
Diode dv/dt ruggedness	dv/dt	Turn-on slew rate, repetitive	200	V/ns
Power dissipation	P _{tot**}	T _C =25 °C	1689	W
Operating junction temperature	Tj		-40150	°C
Storage temperature	T _{storage}		-40150	°C

Notes:

^{*} Typical Rth_{JC} used

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Electrical Characteristics, at T_j=25 °C, unless otherwise specified

Characteristics	Symbol	Conditions	Values			l lmi4
			min.	typ.	max.	Unit
DC blocking voltage	V _{DC}	I _R =800uA, T _j =25 °C	1200	-	-	V
		I _F =400A, T _j =25 °C	-	1.67	1.90	
Diode forward voltage	V _F **	I _F =400A, T _j =125 °C	-	2.04	-	V
		I _F =400A, T _j =150 °C	-	2.17	2.70	
Reverse current		V _R =1,200V, T _j =25 °C	-	42	800	
		V _R =1,400V, T _j =25 °C	-	254	-	
	I _R	V _R =1,200V, T _j =125 °C	-	339	-	μА
		V _R =1,200V, T _j =150 °C	-	652	6000	
Total capacitive charge	Q _C	V _R =800V, T _j =25 °C	-	2450	-	nC
Total capacitance	С	V _R =1V, f=1 MHz	-	33.8	-	nF
		V _R =400V, f=1 MHz	-	2.4	-	
		V _R =800V, f=1 MHz	-	1.7	-	

Thermal and Package Characteristics, at T_j=25 °C, unless otherwise specified

Characteristics S	Symbol	Conditions	Values			Unit
Citatacteristics	Syllibol	Conditions	min.	typ.	max.	Oille
Thermal resistance, junction-case	R _{thJC}	Per leg	-	0.07	0.09	°C/W
Mounting torque	M _d		-	-	5.0	N-m
Terminal connection torque	M _{dt}		-	-	5.0	N-m
Package weight	W _t		-	250	-	g
Isolation voltage	V _{ISOL}	I _{ISOL} < 1mA, 50/60 Hz, 1 min	2500	-	-	V

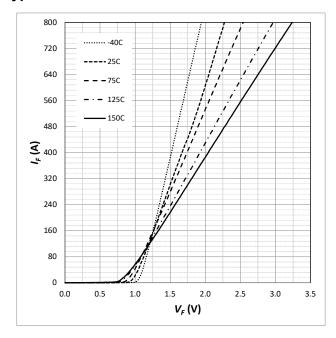
NTC Characteristics, at T_i =25 °C, unless otherwise specified

Characteristics	Symbol	Conditions —	Values			Unit
Characteristics	Syllibol		min.	typ.	max.	Oilit
Rated resistance	R _{NTC}	$T_{NTC} = 25^{\circ}C$	-	5.0	-	kΩ
Resistance tolerance	ΔR/R		-5	-	5	%
Beta Value (T ₂ = 50°C)	β _{25/50}		-	3380	-	k
Beta Value (T ₂ = 80°C)	β _{25/80}		-	3440	-	k
Power dissipation	P _{MAX}	T _{NTC} = 25°C	-	-	50	mW

^{**}Diode forward voltage measured at module terminals

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Typical Performance



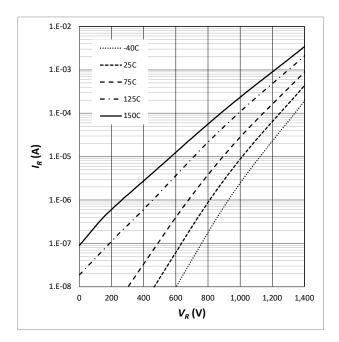


Fig. 1 Forward Characteristics (parameterized on T_i)

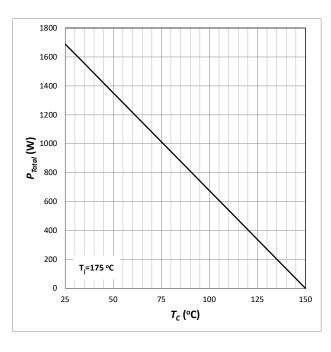


Fig. 2 Reverse Characteristics (parameterized on $\boldsymbol{T_j})$

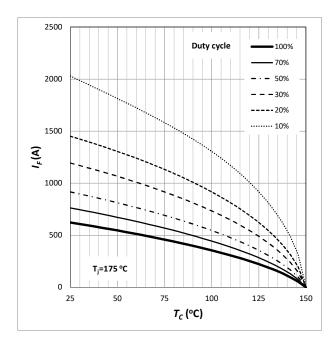
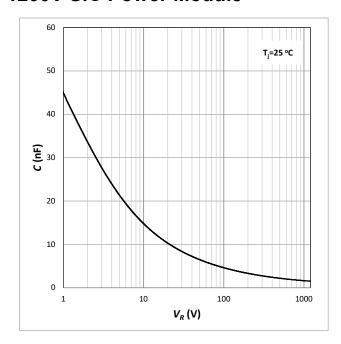


Fig. 3 Power Derating

Fig. 4 Current Derating

1200V SiC Power Module

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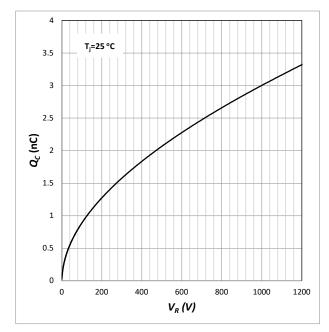


Fig. 5 Capacitance

1.6
1.4
1.2
1
1.2
1
0.8
0.6
0.4
0.2
0
0
200
400
600
800
1000
1200

Fig. 6 Capacitive Charge

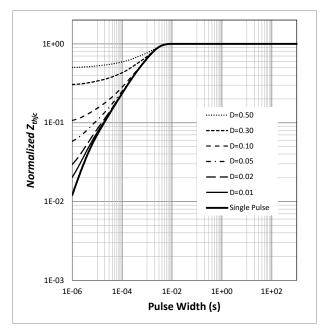


Fig. 7 Typical Capacitance Stored Energy

Fig. 8 Transient Thermal Impedance

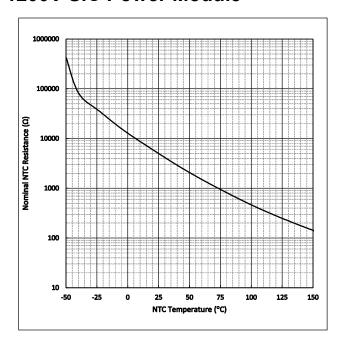
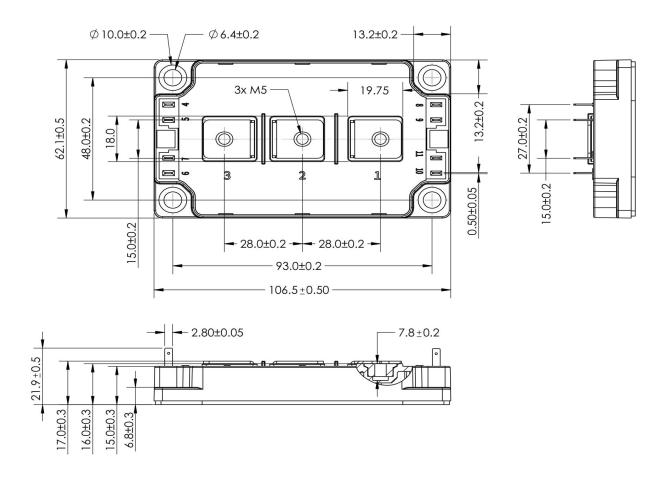


Fig. 9 Nominal NTC Resistance vs. Temperature

Package Dimensions S7



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Revision History

Date	Revision	Notes
8/20/2020	0.1	Initial release of preliminary datasheet
9/17/2021	0.2	Update specs
11/24/2021	0.3	Updated package image
4/11/2022	1.0	Initial production release

<u>Notes</u>

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

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